

4AC12

Silicon NPN Epitaxial

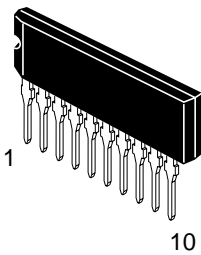
HITACHI

Application

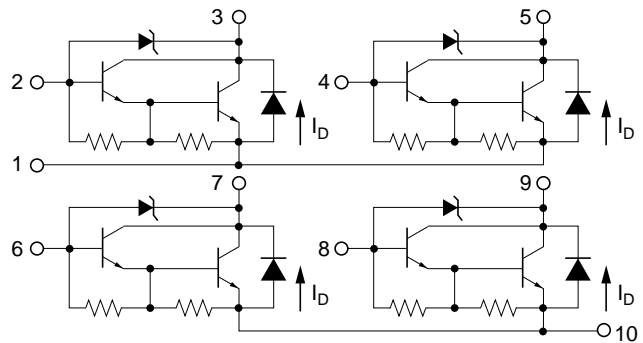
Low frequency power amplifier

Outline

SP-10



- 1, 10 Emitter
- 2, 4, 6, 8 Base
- 3, 5, 7, 9 Collector



4AC12

Absolute Maximum Ratings (for each device, $T_a = 25^\circ\text{C}$)

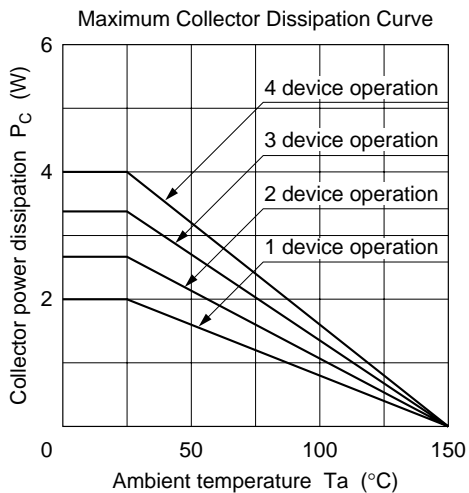
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	27	V
Collector to emitter voltage	V_{CEO}	27	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_{C}	2	A
Collector peak current	$I_{\text{C(peak)}}$	4	A
Diode current	I_{D}	2	A
Collector power dissipation	P_{C}^{*1}	4	W
	$P_{\text{C}}^{*1} (T_{\text{C}} = 25^\circ\text{C})$	28	
Junction temperature	T_{J}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note: 1. 4 devices operation.

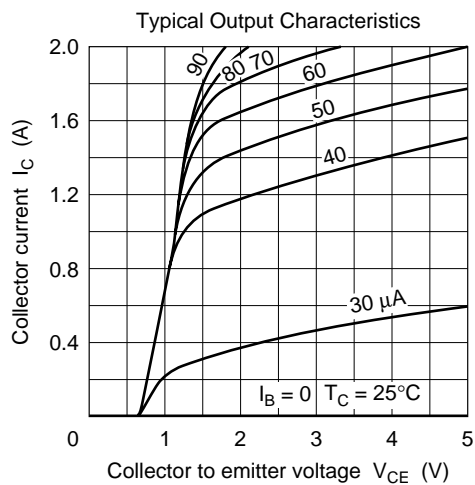
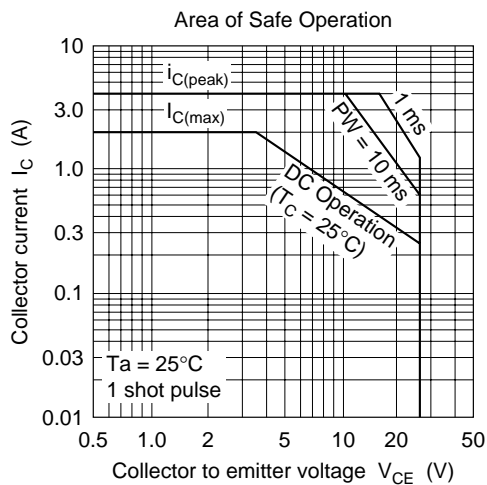
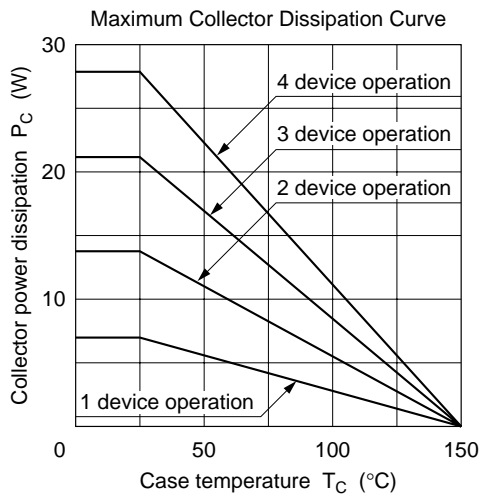
Electrical Characteristics (for each device, $T_a = 25^\circ\text{C}$)

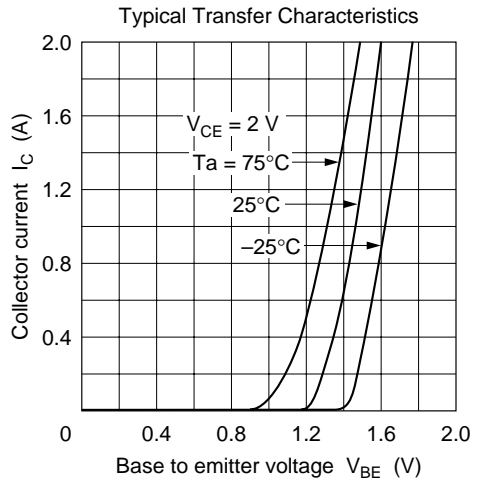
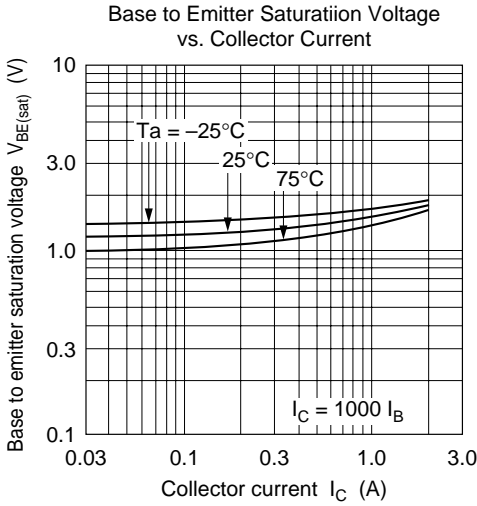
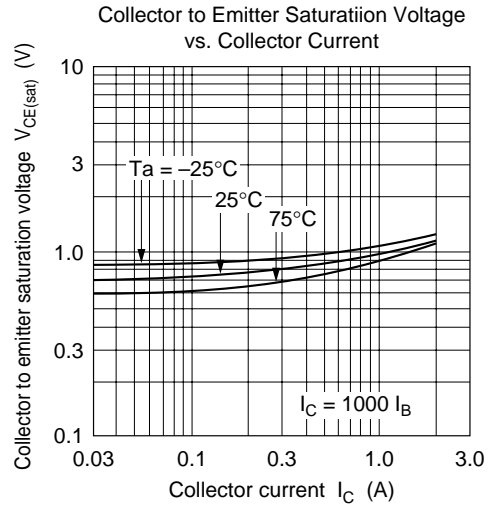
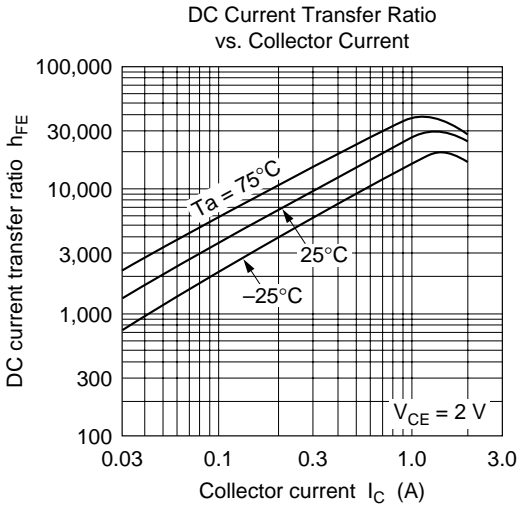
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CBO}}$	27	—	—	V	$I_{\text{C}} = 1 \text{ mA}, I_{\text{E}} = 0$
Collector to emitter sustain voltage	$V_{\text{CEO}(\text{SUS})}$	28	—	36	V	$I_{\text{C}} = 1 \text{ A}, L = 20 \text{ mH}, R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	7	—	—	V	$I_{\text{E}} = 5 \text{ mA}, I_{\text{C}} = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0$
	I_{CEO}	—	—	10		$V_{\text{CE}} = 20 \text{ V}, R_{\text{BE}} = \infty$
DC current transfer ratio	h_{FE}	7000	—	30000		$V_{\text{CE}} = 2 \text{ V}, I_{\text{C}} = 0.5 \text{ A}$
	h_{FE}	2000	—	—		$V_{\text{CE}} = 2 \text{ V}, I_{\text{C}} = 2 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	—	—	1.5	V	$I_{\text{C}} = 2 \text{ A}, I_{\text{B}} = 2 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	—	—	2.0	V	$I_{\text{C}} = 2 \text{ A}, I_{\text{B}} = 2 \text{ mA}^{*1}$
C to E diode forward current	V_{D}	—	—	3.5	V	$I_{\text{D}} = 2 \text{ A}$

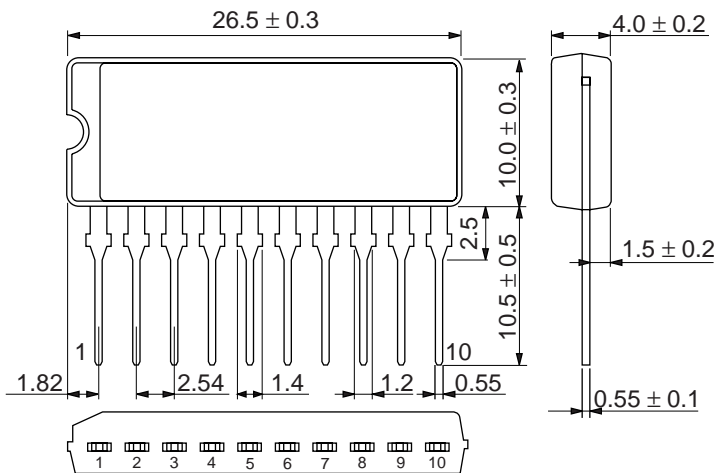
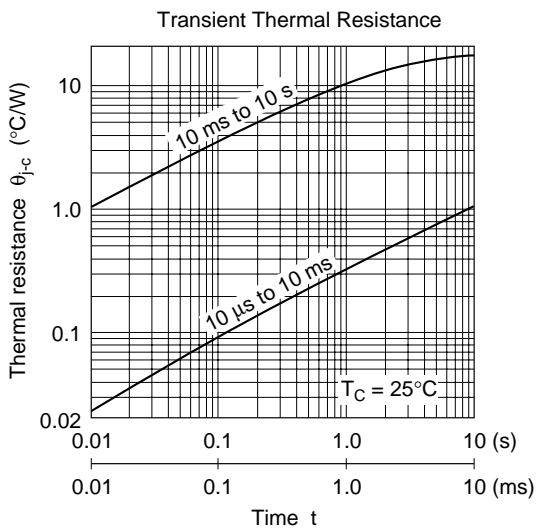
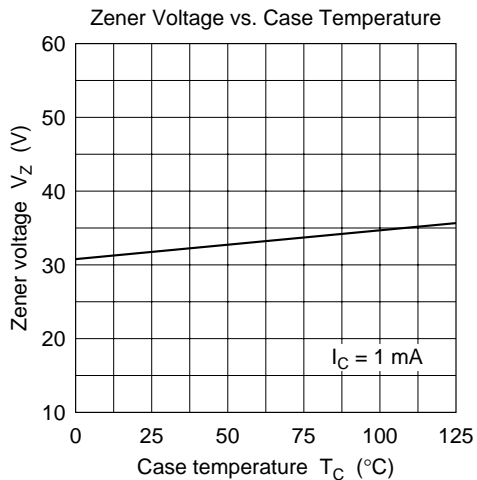
Note: 1. Pulse test.



Note: Collector power dissipation of each devices is identical.

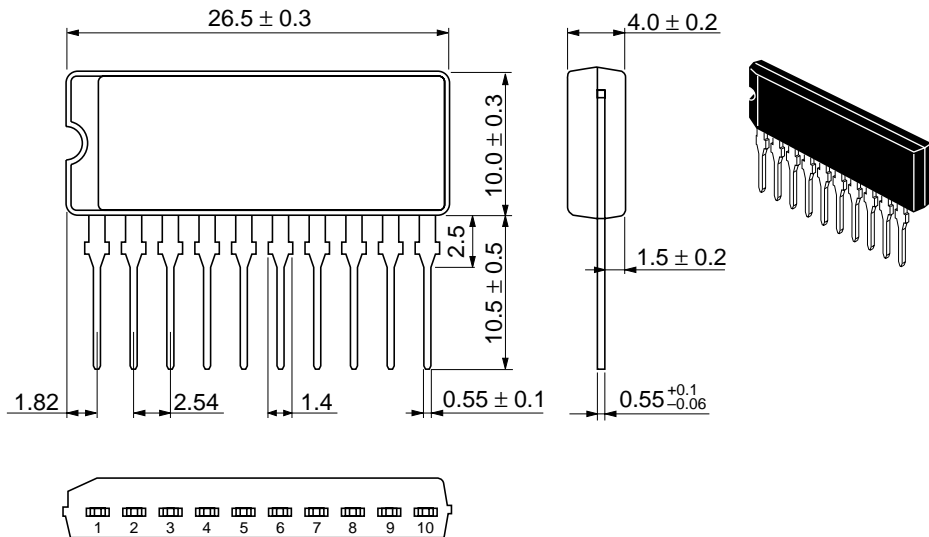






Pin No.	1	2	3	4	5	6	7	8	9	10
Electrode	E	B	C	B	C	B	C	B	C	E

Note: B: Base
 C: Collector
 E: Emitter



Hitachi Code	SP-10
JEDEC	—
EIAJ	—
Weight (reference value)	2.9 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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